



PTD958G/PTU958G

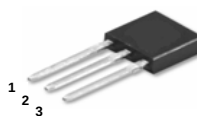
PNP Epitaxial Silicon Transistor

- 5 Amperes / 20 Watts

Audio Power Amplifier

- Low speed switching

PTU958G
I-PAK(TO-251)



1. Base
2. Collector
3. Emitter

PTD958G
D-PAK(TO-252)



1. Base
2. Collector
3. Emitter

Absolute Maximum Ratings $T_A=25^{\circ}\text{C}$ unless otherwise noted

CHARACTERISTICS	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-7.0	V
Collector Current (DC)	I_C	-5.0	A
Collector Dissipation ($T_c=25^{\circ}\text{C}$)	P_C	20	W
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~150	$^{\circ}\text{C}$

Electrical Characteristics $T_A=25^{\circ}\text{C}$ unless otherwise noted

CHARACTERISTICS	SYMBOL	Test Condition	Min	Typ.	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-100\mu\text{A}, I_E=0$	-40	--	--	V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-1\text{mA}, I_B=0$	-30	--	--	V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_C=-100\mu\text{A}, I_E=0$	-7.0	--	--	V
Collector Cut-off Current	I_{CBO}	$V_{EB}=-40\text{V}, I_C=0$	--	--	-500	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$	--	--	-500	nA
DC Current Gain	h_{FE1}	$V_{CE}=-2\text{V}, I_C=-0.5\text{A}$	200	--	400	--
	h_{FE2}	$V_{CE}=-1\text{V}, I_C=-3.0\text{A}$	30	--	--	--
Collector-Emitter Saturation Voltage	$V_{CE(sat)1}$	$I_C=-4.0\text{A}, I_B=-0.4\text{A}$	--	-0.18	-0.4	V
	$V_{CE(sat)2}$	$I_C=-3.0\text{A}, I_B=-0.15\text{A}$	--	-0.18	-0.35	V
Base-Emitter Saturation Voltage	$V_{BE(sat)1}$	$I_C=-4.0\text{A}, I_B=-0.40\text{A}$	--	-0.98	-1.4	V
	$V_{BE(sat)1}$	$I_C=-3.0\text{A}, I_B=-0.15\text{A}$	--	-0.90	-1.2	V
Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}, f=1\text{MHz}$	--	53	--	pF
Current Gain Bandwidth Product	f_T	$V_{CE}=-10\text{V}, I_C=-50\text{mA}$	--	152	--	MHz

Typical Characteristics

